

## TO-92L Plastic-Encapsulate Transistors

### 3CG8551 TRANSISTOR (PNP)

#### FEATURES

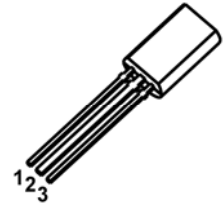
- General Purpose Switching Application
- Complementary to 3DG8051

#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-2	A
$P_C$	Collector Power Dissipation	750	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	167	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

#### TO - 92L

1. EMITTER
2. COLLECTOR
3. BASE



#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CE}=-40\text{V}, I_B=0$			-2	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE}=-2\text{V}, I_C=-0.1\text{A}$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-1\text{A}, I_B=-0.1\text{A}$			-1	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}, I_C=-50\text{mA}, f=100\text{MHz}$	150			MHz